

This diagram shows a cross-sectional view of a semiconductor device. It features a central channel region (12) flanked by side regions (2). The device is built on a substrate (3). The top surface is covered by a layer (3) with a central opening. The side regions (2) are separated from the central channel (12) by a vertical boundary. The substrate (3) is shown at the bottom, with a central region (12) and side regions (2) extending upwards.

This cross-sectional view shows a central layer 4, which is a light-colored rectangle. Above it is a thin layer 5. Below layer 4 is a thick, cross-hatched layer 12. This layer 12 is supported by a base consisting of a bottom layer 3 and a middle layer 2. The middle layer 2 has several rectangular openings or notches. The top layer 5 is wider than the central layer 4 and extends over the edges of the cross-hatched layer 12.

Fig. 1 is a cross-sectional view of a semiconductor device. It shows a substrate with multiple layers: a top layer (2), a middle layer (12), and a bottom layer (3). A central structure (4) is formed on the substrate, with side contacts (5, 17) on its left and right sides. The device is shown in a cross-sectional view, with the central structure (4) being a rectangular block. The side contacts (5, 17) are located on the left and right sides of the central structure (4). The substrate layers are labeled 2, 12, and 3 from top to bottom. The central structure (4) is a rectangular block. The side contacts (5, 17) are located on the left and right sides of the central structure (4).

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Fig. 2A Prior Art

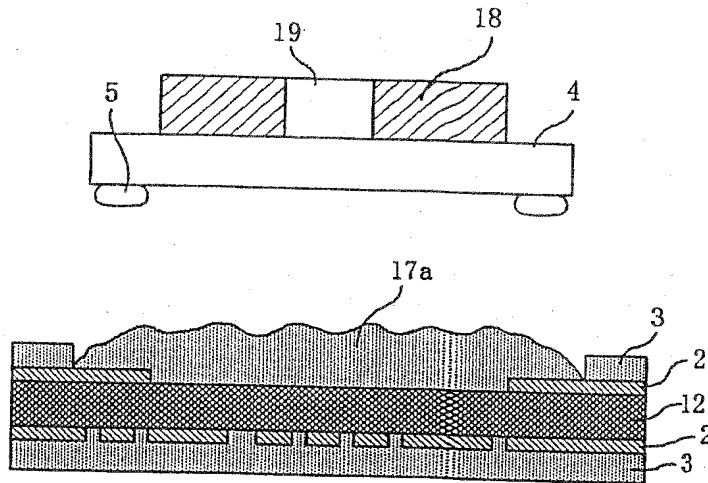
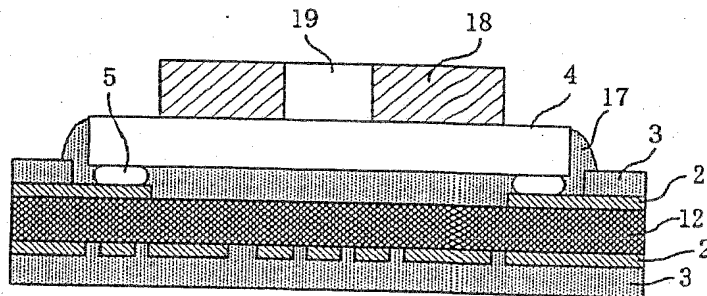


Fig. 2B Prior Art



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Fig. 3A Prior Art

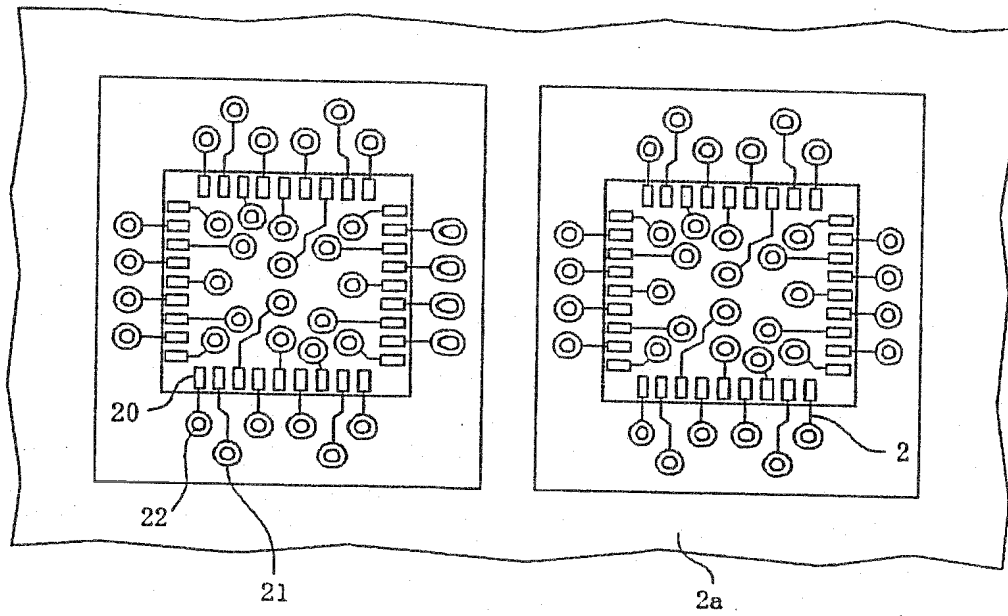
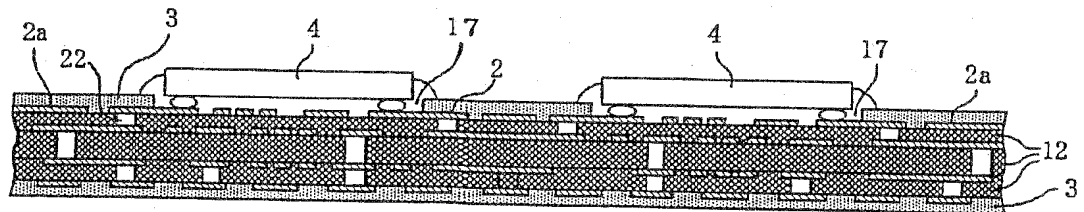


Fig. 3B Prior Art



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Fig. 4A Prior Art

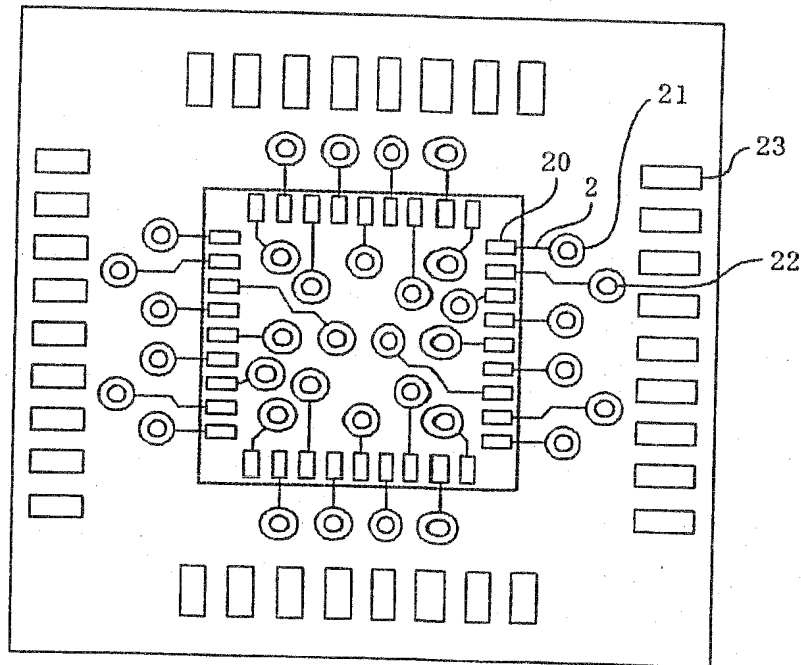


Fig. 4B Prior Art

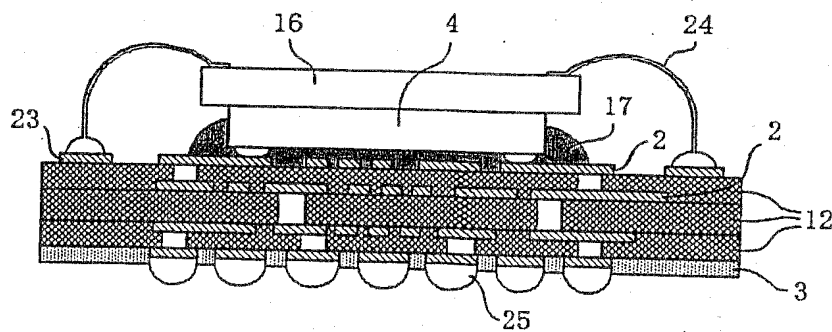


Fig. 5 Prior Art

